NSN 5961-01-087-9486 Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-087-9486
Inclosure Material:
Metal
Overall Length:
0.185 inches
Overall Diameter:
0.370 inches
Component Name And Quantity:
2 transistor
Mounting Method:
Terminal
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
45.0 collector to base voltage, dc all transistor and 45.0 collector to emitter voltage, dc all transistor and 6.0 forward voltage, peak all
transistor
Power Rating Per Characteristic:
800.0 milliwatts small-signal input power, common-collector preset all transistor
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius junction
Special Features:
All transistor junction pattern arrangement: npn
Test Data Document:
49956-953029 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
6 uninsulated wire lead
Shelf Life:
N/a
Unit Of Measure:
<del></del>
Demilitarization:
No
Fiig:
A110a0